

up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

43. (amended) The method of claim 40 wherein the conductive layer is formed on the first electrode, further comprising chemisorbing additional alternating first and second precursor layers before forming the dielectric layer.

44. (amended) The method of claim 40 wherein the conductive layer comprises elemental metal, a metal alloy, or a metal containing compound.

48. (new) The method of claim 1 wherein the substrate comprises a semiconductive wafer.

49. (new) The method of claim 1 wherein the first capacitor electrode comprises HSG polysilicon.

50. (new) The method of claim 49, wherein the atomic layer deposited barrier layer comprises TiN and the first capacitor electrode further comprises the TiN.

51. (new) The method of claim 1 wherein the atomic layer deposited barrier layer comprises TiN.

52. (new) The method of claim 1 wherein the capacitor dielectric layer comprises Al_2O_3 .

53. (new) The method of claim 1 wherein the second capacitor electrode comprises TiN.

54. (new) The method of claim 1 wherein the first capacitor electrode comprises HSG polysilicon, the atomic layer deposited barrier layer comprises TiN, the capacitor dielectric layer comprises Al_2O_3 , and the second capacitor electrode comprises TiN.

55. (new) The method of claim 13 wherein the substrate comprises a semiconductive wafer.

56. (new) The method of claim 13 wherein the first capacitor electrode comprises HSG polysilicon.

57. (new) The method of claim 56, wherein the barrier layer comprises TiN and the first capacitor electrode further comprises the TiN.

58. (new) The method of claim 13 wherein the barrier layer comprises TiN.

59. (new) The method of claim 13 wherein the capacitor dielectric layer comprises Al_2O_3 .

60. (new) The method of claim 13 wherein the second capacitor electrode comprises TiN.

61. (new) The method of claim 13 wherein the first capacitor electrode comprises HSG polysilicon, the barrier layer comprises TiN, the capacitor dielectric layer comprises Al_2O_3 , and the second capacitor electrode comprises TiN.
62. (new) The method of claim 34 wherein the substrate comprises a semiconductive wafer.
63. (new) The method of claim 34 wherein the first capacitor electrode comprises HSG polysilicon.
64. (new) The method of claim 63, wherein the atomic layer deposited conductive layer comprises TiN and the first capacitor electrode further comprises the TiN.
65. (new) The method of claim 34 wherein the atomic layer deposited conductive layer comprises TiN.
66. (new) The method of claim 34 wherein the capacitor dielectric layer comprises Al_2O_3 .
67. (new) The method of claim 34 wherein the second capacitor electrode comprises TiN.
68. (new) The method of claim 34 wherein the first capacitor electrode comprises HSG polysilicon, the atomic layer deposited conductive layer comprises TiN, the capacitor dielectric layer comprises Al_2O_3 , and the second capacitor electrode comprises TiN.

69. (new) The method of claim 40 wherein the substrate comprises a semiconductive wafer.
70. (new) The method of claim 40 wherein the first capacitor electrode comprises HSG polysilicon.
71. (new) The method of claim 70, wherein the conductive layer comprises TiN and the first capacitor electrode further comprises the TiN.
72. (new) The method of claim 40 wherein the conductive layer comprises TiN.
73. (new) The method of claim 40 wherein the capacitor dielectric layer comprises Al_2O_3 .
74. (new) The method of claim 40 wherein the second capacitor electrode comprises TiN.
75. (new) The method of claim 40 wherein the first capacitor electrode comprises HSG polysilicon, the conductive layer comprises TiN, the capacitor dielectric layer comprises Al_2O_3 , and the second capacitor electrode comprises TiN.